Ordering number: EN 1943A

SANYO

No.1943A

2SA1392/2SC3383

PNP/ NPN Epitaxial Planar Silicon Transistors

AF Amp Applications

Features

- Adoption of FBET process
- AF amp

( ): 2SA1392

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CBO}	(-)60	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)6	V
Collector Current	I_C	(-)200	mA
Collector Current (Pulse)	I_{CP}	(-)400	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

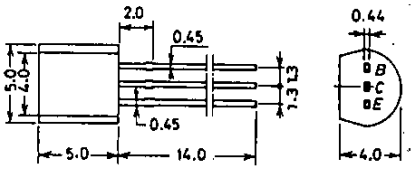
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)40V, I_E=0			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)5V, I_C=0			(-)0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=(-)6V, I_C=(-)1mA	100*		560*	
	$h_{FE(2)}$	V_{CE}=(-)6V, I_C=(-)0.1mA	70			
Gain-Bandwidth Product	f_T	V_{CE}=(-)6V, I_C=(-)10mA		250		MHz
				(200)		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)100mA, I_B=(-)10mA			(-)0.3	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=(-)100mA, I_B=(-)10mA			(-)1.0	V
Output Capacitance	C_{ob}	V_{CB}=(-)6V, f=1MHz		2.7		pF
				(3.7)		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=(-)10μA, I_E=0	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=(-)1mA, R_{BE}=∞	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=(-)10μA, I_C=0	(-)6			V

*: The 2SA1392/2SC3383 are classified by 1mA h_{FE} as follows:

100 R 200	140 S 280	200 T 400	280 U 560

Package Dimensions 2003A
(unit: mm)



JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN